



Power Rectifier Diodes

Features

- Full blocking capability over wide temperature range
- Hermetically sealed ceramic package
- High case non-rupture current

Applications

- Uncontrolled Rectifiers
- Welding

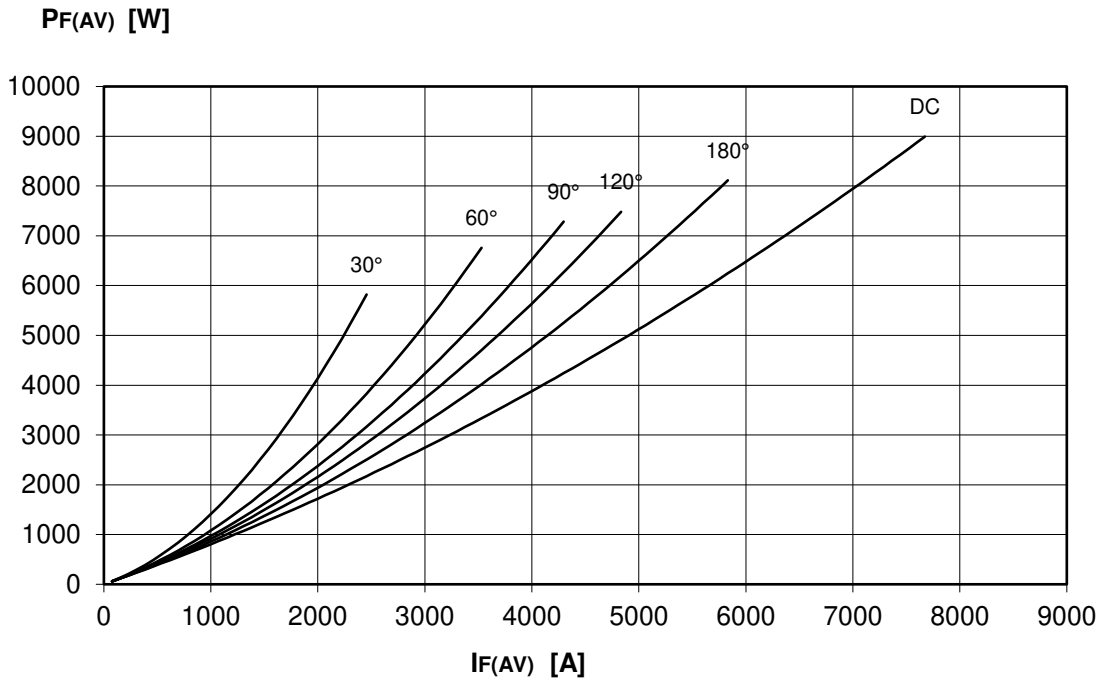
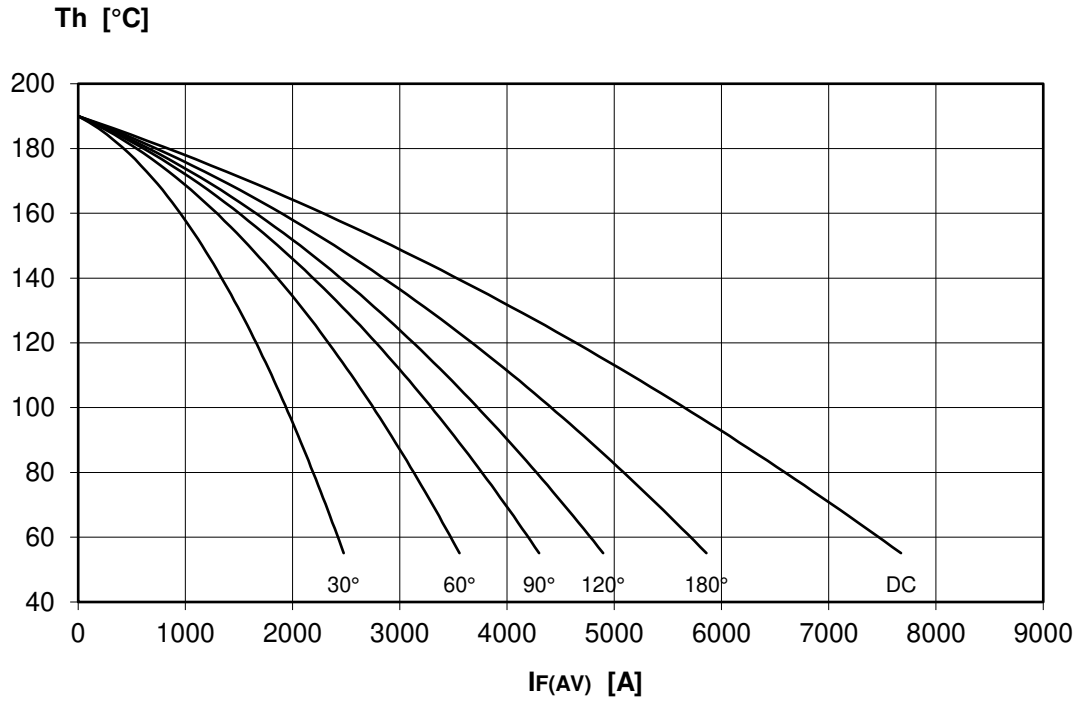
Key Parameters

V_{RRM}	= 1000V
$I_{F(AV)}$	= 5836A
I_{FSM}	= 50400A
$V_{F(TO)}$	= 0.75V
r_F	= 0.055m Ω

Symbol	Characteristic	Conditions	T _j [°C]	Value	Unit
BLOCKING					
V_{RRM}	Repetitive peak reverse voltage		190	1000	V
V_{RSM}	Non-repetitive peak reverse voltage		190	1100	V
I_{RRM}	Repetitive peak reverse current	V=VRRM	190	75	mA
CONDUCTING					
$I_{F(AV)}$	Mean forward current	180° sin, 50 Hz, Th=55°C, double side cooled		5836	A
$I_{F(AV)}$	Mean forward current	180° sin, 50 Hz, Tc=85°C, double side cooled		6457	A
I_{FSM}	Surge forward current	Sine wave, 10 ms without reverse voltage	190	50,4	kA
$I^2 t$	$I^2 t$			12701 x 10 ³	A ² s
V_{FM}	Forward voltage	Forward current = 4500 A	25	1,16	V
$V_{F(TO)}$	Threshold voltage		190	0,75	V
r_F	Forward slope resistance		190	0,055	mohm
SWITCHING					
t_{rr}	Reverse recovery time		190		μ s
Q_{rr}	Reverse recovery charge				μ C
I_{rr}	Peak reverse recovery current				A
MOUNTING					
$R_{th(j-h)}$	Thermal impedance, DC	Junction to heatsink, double side cooled		15,0	°C/kW
$R_{th(c-h)}$	Thermal impedance	Case to heatsink, double side cooled		5,0	°C/kW
T_j	Operating junction temperature			-30 / 190	°C
F	Mounting force			22.0 / 24.5	kN
	Mass			200	g

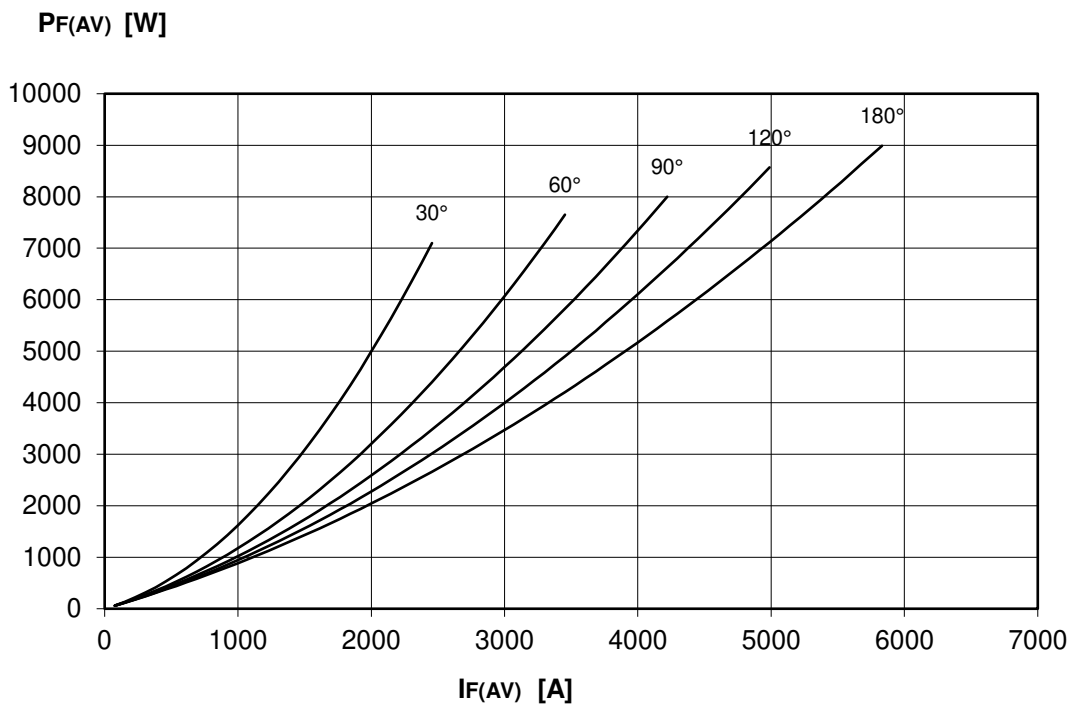
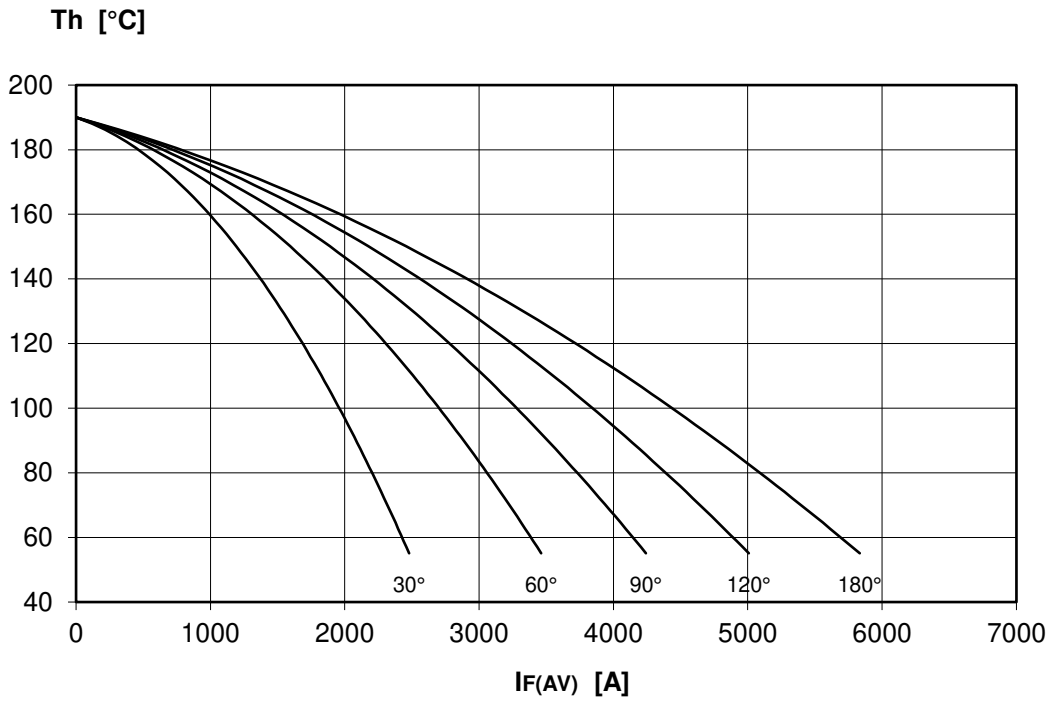
DISSIPATION CHARACTERISTICS

SQUARE WAVE

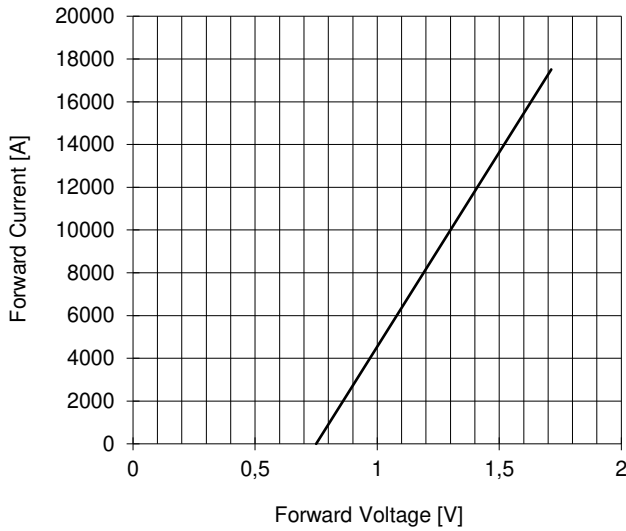


DISSIPATION CHARACTERISTICS

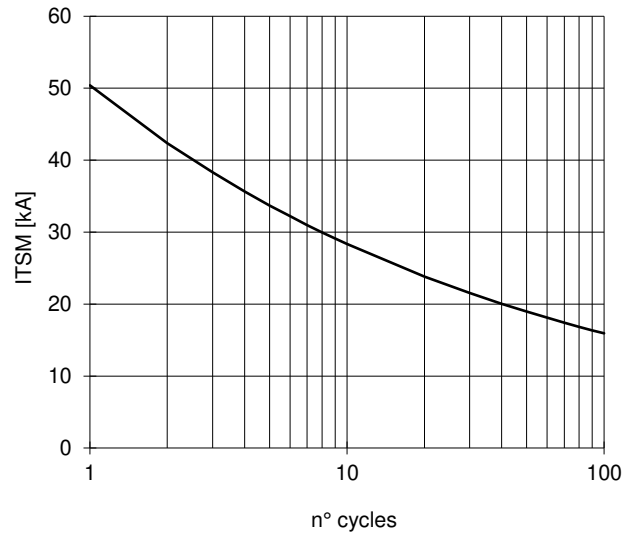
SINE WAVE



FORWARD CHARACTERISTIC
T_j = 190 °C



SURGE CHARACTERISTIC
T_j = 190 °C



TRANSIENT THERMAL IMPEDANCE
DOUBLE SIDE COOLED

